Maryam Amirhoseiny

List of Publications by Year
in descending order

27	200	1040056 9	1058476 14
papers	citations	h-index	g-index

27	27	27	142
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Effect of different EBL structures on deep violet InGaN laser diodes performance. Optics and Laser Technology, 2016, 76, 106-112.	4.6	29
2	Characterizations of InN Thin Films Grown on Si (110) Substrate by Reactive Sputtering. Journal of Nanomaterials, 2011, 2011, 1-7.	2.7	26
3	Synthesis of CuS Nanoparticles by Laser Ablation Method in DMSO Media. Journal of Cluster Science, 2017, 28, 2753-2764.	3.3	21
4	Fabrication of InN based photodetector using porous silicon buffer layer. Surface Engineering, 2013, 29, 772-777.	2.2	15
5	Effect of annealing temperature on IR-detectors based on InN nanostructures. Vacuum, 2014, 106, 46-48.	3.5	13
6	Photoluminescence spectra of nitrogen-rich InN thin films grown on Si(110) and photoelectrochemical etched Si(110). Vacuum, 2014, 101, 217-220.	3.5	12
7	Comparative study on structural and optical properties of nitrogen rich InN on Si(110) and 6H-SiC. Surface Engineering, 2013, 29, 561-565.	2.2	11
8	InN PHOTOCONDUCTORS ON DIFFERENT ORIENTATIONS OF Si SUBSTRATES. International Journal of Modern Physics B, 2012, 26, 1250137.	2.0	9
9	STRUCTURE AND OPTICAL PROPERTIES OF InN THIN FILM GROWN ON SiC BY REACTIVE RF MAGNETRON SPUTTERING. Surface Review and Letters, 2013, 20, 1350008.	1.1	9
10	Growth of InN thin films on different Si substrates at ambient temperature. Microelectronics International, 2013, 30, 63-67.	0.6	8
11	Effect of deposition conditions on properties of nitrogen rich-InN nanostructures grown on anisotropic Si (110). Materials Science in Semiconductor Processing, 2015, 35, 216-221.	4.0	8
12	The effect of AlGaN bulk and AlGaN/GaN superlattice cladding layers on performance characteristics of deep violet InGaN DQW lasers. Vacuum, 2017, 141, 139-143.	3.5	7
13	Optical properties of photo-electrochemical etching of anisotropic silicon (110). IEICE Electronics Express, 2012, 9, 752-757.	0.8	6
14	Synthesis of nanocrystalline In2O3 on different Si substrates at wet oxidation environment. Optik, 2013, 124, 2679-2681.	2.9	6
15	EFFECT OF CURRENT DENSITY ON OPTICAL PROPERTIES OF ANISOTROPIC PHOTOELECTROCHEMICAL ETCHED SILICON (110). Modern Physics Letters B, 2012, 26, 1250131.	1.9	5
16	Effect of QW thickness and numbers on performance characteristics of deep violet InGaN MQW lasers. International Journal of Modern Physics B, 2015, 29, 1550081.	2.0	5
17	Induced magnetic anisotropy in Fe0.7Co0.3fine particles. Journal Physics D: Applied Physics, 2006, 39, 4925-4929.	2.8	2
18	Dependence of output emission wavelength and LD performance on barriers material and thickness. Optik, 2016, 127, 4815-4818.	2.9	2

#	Article	IF	Citations
19	Performance characteristics of deep violet InGaN DQW lasers based on different compliance layers. Optik, 2017, 131, 194-200.	2.9	2
20	A Simple Method to Prepare Indium Oxide Nanoparticles on Si (110). Advanced Materials Research, 0, 620, 193-197.	0.3	1
21	Effects of Cavity Length on Optical Characteristics of Deep Violet InGaN DQW Lasers. Advanced Materials Research, 2012, 626, 605-609.	0.3	1
22	Nanoporous all metallic binder free Sn:Pb composite electrode for high performance supercapacitors. Microelectronic Engineering, 2016, 157, 31-34.	2.4	1
23	Carbon nanotube-based supercapacitors using low cost collectors. Modern Physics Letters B, 2016, 30, 1550272.	1.9	1
24	Reactive Sputtering Growth and Characterizations of InN Thin Films on Si Substrates. Advanced Materials Research, 2012, 545, 290-293.	0.3	0
25	INFLUENCE OF WAVEGUIDE LAYERS ON DEEP VIOLET InGaN DQW LASERS PERFORMANCE. Surface Review and Letters, 2015, 22, 1550051.	1.1	0
26	A SIMPLE METHOD TO PREPARE NANOPOROUSSn:PbCOMPOSITE METAL FOAM. Surface Review and Letters, 2015, 22, 1550034.	1.1	0
27	Doping effects in p- and n-type layers of 390-nm InGaN DQW lasers. International Journal of Modern Physics B, 2015, 29, 1550118.	2.0	0